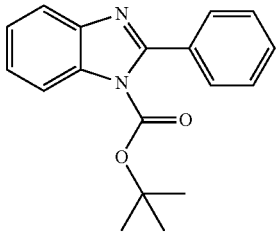
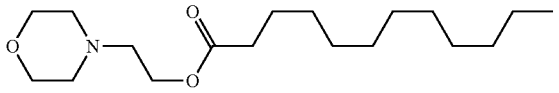
Comparative Quenchers 1 to 7 of the Following Structural Formulae

**[0176]**

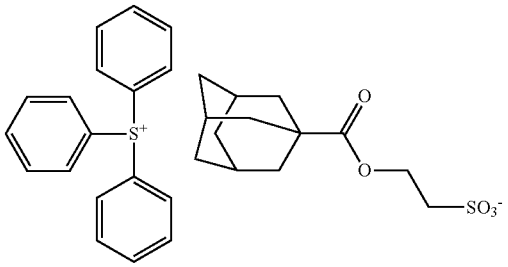
Comparative Quencher 1



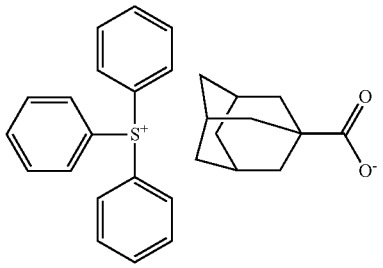
Comparative Quencher 2



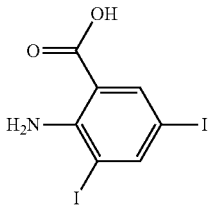
Comparative Quencher 3



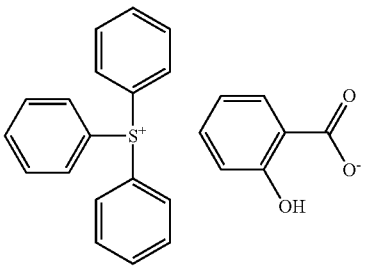
Comparative Quencher 4



Comparative Quencher 5



Comparative Quencher 6



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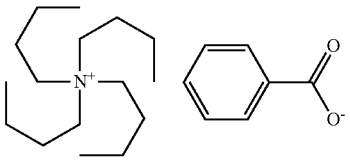
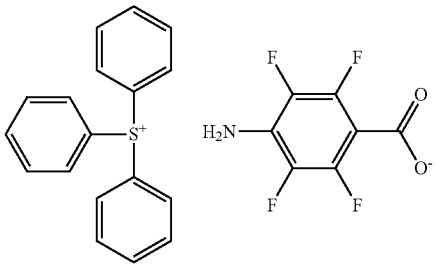
Comparative Quencher 7



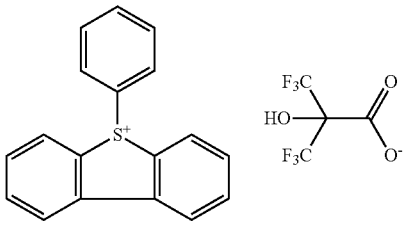
Blend Quenchers 1 to 3 of the Following Structural Formulae

**[0177]**

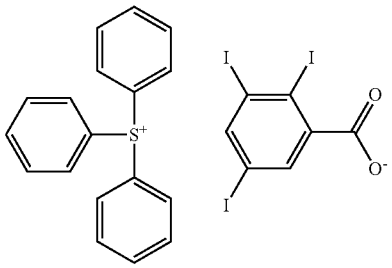
Blend Quencher 1



Blend Quencher 2



Blend Quencher 3



(2) EUV Lithography Test

**[0178]** Each of the resist compositions in Tables 1 to 4 was spin coated on a silicon substrate having a 20-nm coating of silicon-containing spin-on hard mask SHB-A940 (Shin-Etsu Chemical Co., Ltd., silicon content 43 wt %) and prebaked on a hotplate at 105° C. for 60 seconds to form a resist film of 60 nm thick. Using an EUV scanner NXE3300 (ASML, NA 0.33, σ 0.9/0.6, quadrupole illumination), the resist film was exposed to EUV through a mask bearing a hole pattern at a pitch 46 nm (on-wafer size) and +20% bias. The resist film was baked (PEB) on a hotplate at the temperature shown in Tables 1 to 4 for 60 seconds and developed in a 2.38 wt % TMAH aqueous solution for 30 seconds to form